Part Number	Customer

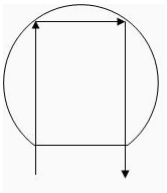
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	NONE	
	5.0	Overall Thickness	380.50 +/- 10.50 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ESTIMATE. ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ESTIMATE. ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Edge Rounding	Semi Standard Edge Rounding.	Guaranteed by process
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	350.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Lapped with oxide and laser mark SEMI M-13.	Guaranteed by process
	19.0	Backside Lasermark	IceMOS Standard Scribe format,alpha-numberic: YYMM-XXXXX. No duplicates.	Guaranteed by process
	20.0	Backside Oxide thickness	2,500.00 +/- 250.00 A	Guaratneed by process, thickness ref. Front Field Oxide
BuriedOxide	21.0	Oxide Type	Thermal	
	22.0	Oxide Thickness	5,000.00 +/- 250.00 A	Nanospec centre point, 4%
	23.0	Oxide formed on	Handle Wafer	
DeviceSilicon	24.0	Device Growth Method	CZ	Wafer Vendor
	25.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	26.0	Nominal Thickness	30.00 +/- 0.50 µm	30um +/- 0.3um BEST EFFORT. FTIR, 100% 9-Pt (note3)
	27.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	28.0	Device Doping Type	P	Wafer Vendor
	29.0	Device Dopant	Boron	Wafer Vendor
	30.0	Device Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor

Part Number	Customer

Category		Parameter	Specification	Measurement Method
DeviceSilicon	31.0	Device Field Oxidation	2,500.00 +/- 250.00 A	Nanospec centre point, 4%
	32.0	Dislocation Etch Pit Density	<100 / cm2	Wafer vendor
	33.0	Oxygen Concentration	<15 ppma (ASTM F121-83)	Wafer vendor
	34.0	Voids	none	Bright Light, 100% (note 2)
	35.0	Scratches	0	Bright Light, 100% (note 2)
	36.0	Haze	none	Bright Light, 100% (note 2)

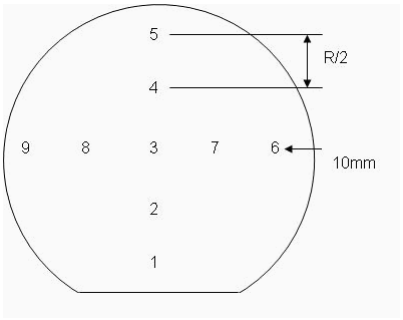
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information